2SD1895

Silicon NPN triple diffusion planar type darlington

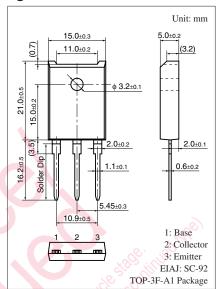
For power amplification Complementary to 2SB1255

■ Features

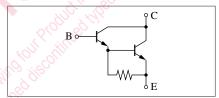
- Optimum for 60 W HiFi output
- High forward current transfer ratio h_{FE}
- Low collector-emitter saturation voltage V_{CE(sat)}
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V_{CBO}	160	V	
Collector-emitter voltage (Base open)	V _{CEO}	140	V	
Emitter-base voltage (Collector open)	V _{EBO}	5	V	
Collector current	I _C	8	A	
Peak collector current	I _{CP}	15	A	
Collector power dissipation	P _C	100	W	
$T_a = 25^{\circ}C$		3		
Junction temperature	T_{j}	150	°C	
Storage temperature	T_{stg}	-55 to +150	°C	
	_			



Internal Connection



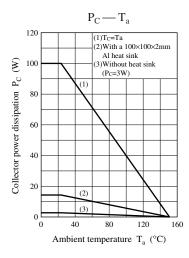
■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

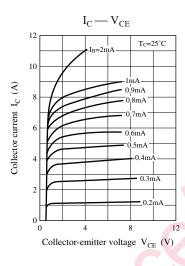
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 30 \text{ mA}, I_B = 0$	140			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 160 \text{ V}, I_E = 0$			100	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 140 \text{ V}, I_{B} = 0$			100	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = 5 \text{ V}, I_C = 0$			100	μΑ
Forward current transfer ratio	h _{FE1}	$V_{CE} = 5 \text{ V}, I_{C} = 1 \text{ A}$	2000			_
	h _{FE2} *	$V_{CE} = 5 \text{ V}, I_{C} = 7 \text{ A}$	5 000		30 000	
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 7 \text{ A}, I_B = 7 \text{ mA}$			2.5	V
Base-emitter saturation voltage	V _{BE(sat)}	$I_C = 7 \text{ A}, I_B = 7 \text{ mA}$			3.0	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_{C} = 0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Turn-on time	t _{on}	$I_C = 7 \text{ A}, I_{B1} = 7 \text{ mA}, I_{B2} = -7 \text{ mA}$		2.0		μs
Storage time	t _{stg}	$V_{CC} = 50 \text{ V}$		6.0		μs
Fall time	t _f			1.2		μs

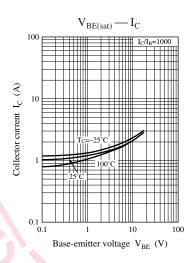
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

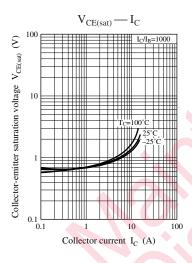
2. *: Rank classification

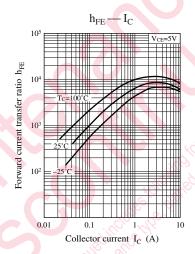
Rank	Q	Р
h _{FE2}	5 000 to 15 000	8 000 to 30 000

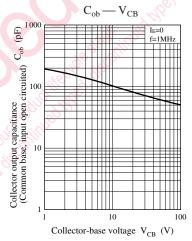


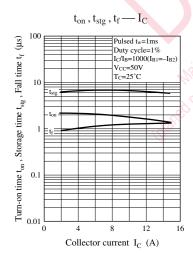


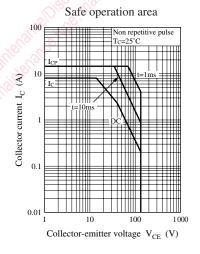












10-3

10-2

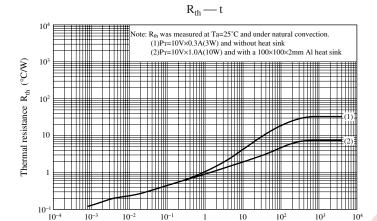
10-1

Time t (s)

10

10²

 10^{3}



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